

4.0 Device Specifications (Continued)

4.2 ABSOLUTE MAXIMUM RATINGS

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-55°C to +125°C
Minimum Ambient Temperature	0°C
Maximum Case Temperature	95°C
V _{CC} with Respect to GND	-0.5V to +6.5V
All Other Pins	-0.5V to (V _{CC} + 0.5)V

4.3 ELECTRICAL CHARACTERISTICS V_{CC} = 5V ± 10%, T_{CASE} = 0° to 95°C, GND = 0V

TABLE 4-2. Electrical Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V _{IH}	Logical 1 Input Voltage		2.0		V _{CC} + 0.5	V
V _{IL}	Logical 0 Input Voltage		-0.5		0.8	V
V _{OH}	Logical 1 Output Voltage	I _{OH} = -400 μA	2.4			V
V _{OL}	Logical 0 Output Voltage	I _{OL} = 6 mA			0.45	V
	DCLK	I _{OL} = 4 mA			0.45	V
	All Other Output Signals					
I _L	Input Load Current	0.45V ≤ V _{IN} ≤ V _{CC}	-20		20	μA
I _{O(OFF)}	Output Leakage Current (Output Signals in TRI-STATE)	0.45V ≤ V _{OUT} ≤ V _{CC}	-20		20	μA
I _{CC}	Active Supply Current	I _{OUT} = 0, T _A = 25°C, V _{CC} = 5.5V		T.B.D.	T.B.D.	mA

Connection Diagram

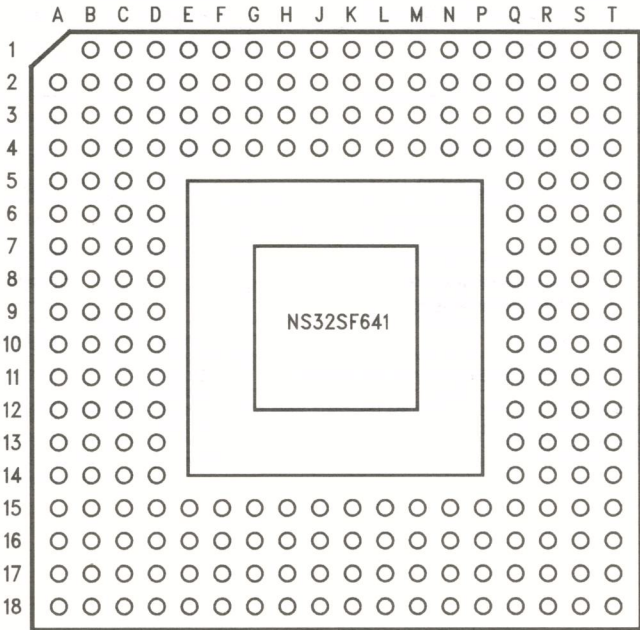


FIGURE 4-2. 223-Pin Ceramic (Plastic for NS32SF640) PGA Package (View from Pin Side)

TL/EE/11191-88

4.0 Device Spe

Signal	P
GND	A1
CLK	A2
N/C	A3
SCLK	A4
CLK	A5
BP	A6
HLDA	A7
PT2	A8
BE7	A9
BE4	A10
BE1	A11
INVDC	A12
ST3	A13
ST1	A14
A0	A15
GND	A16
V _{CC}	A17
GND	B1
BRT	B2
RDY	B3
SHDW	B4
STALL	B5
SDDIN	B6
PFSA	B7
ILO	B8
DRD	B9
BE6	B10
BE3	B11
BE0	B12
CASEC/BW64	B13
ST2	B14
ST0	B15
A1	B16
A2	B17
GND	B18
IDLE	C1
BW0	C2
TRIS	C3
WAIT	C4
ISE	C5
SDIO	C6
PFSB	C7
ERR	C8
DWR0	C9
BE5	C10
BE2	C11
INVBLK	C12
DAK1	C13
DAK0	C14
A3	C15
A4	C16
A5	C17
A6	C18
PIPEN	D1
CIIN	D2
BW1	D3

Note: N/C = Not Connected. N/